

Description

The BSS84 is the high cell density trenched P-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

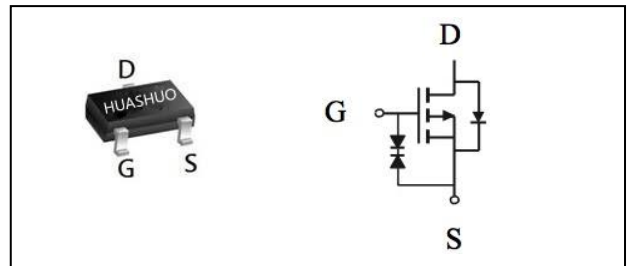
The BSS84 meet the RoHS and Green Product requirement with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	-60	V
$R_{DS(ON),max}$	6	Ω
I_D	-0.3	A

SOT23 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -10V ₁	-0.3	A
$I_D@T_A=100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -10V ₁	-0.24	A
I_{DM}	Pulsed Drain Current ₂	-1	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ₃	0.35	W
T_{STG}	Storage Temperature Range	-40 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-40 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ₁	---	400	$^\circ\text{C/W}$



Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1mA$	---	-0.021	---	V/ $^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-0.2A$	---	4	6	Ω
		$V_{GS}=-4.5V$, $I_D=-0.1A$	---	4.5	7	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.0	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.08	---	mV/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-48V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=-48V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	10	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=-20V$, $I_D=-0.2A$	---	0.18	---	S
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-20V$, $V_{GS}=-10V$, $I_D=-0.2A$	---	1.8	---	nC
Q_{gs}	Gate-Source Charge		---	0.5	---	
Q_{gd}	Gate-Drain Charge		---	0.8	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=-15V$, $V_{GS}=-10V$, $R_G=50\Omega$, $I_D=-0.2A$	---	2.8	---	ns
T_r	Rise Time		---	1	---	
$T_{d(off)}$	Turn-Off Delay Time		---	19	---	
T_f	Fall Time		---	9	---	
C_{iss}	Input Capacitance	$V_{DS}=-25V$, $V_{GS}=0V$, $f=1MHz$	---	170	---	pF
C_{oss}	Output Capacitance		---	53	---	
C_{rss}	Reverse Transfer Capacitance		---	9	---	

Diode Characteristics

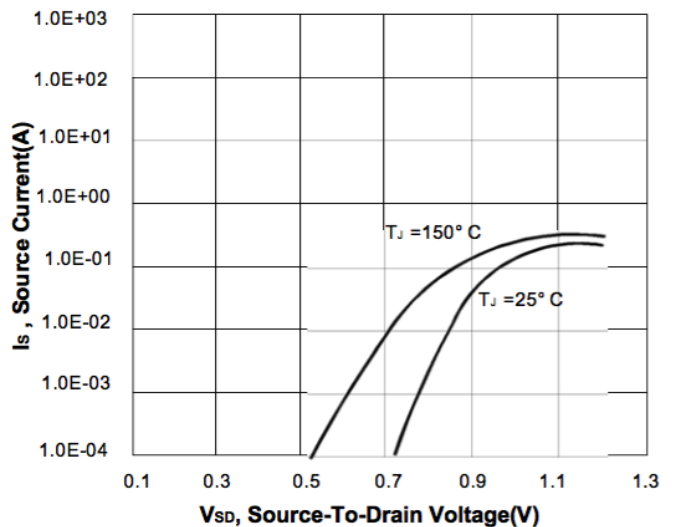
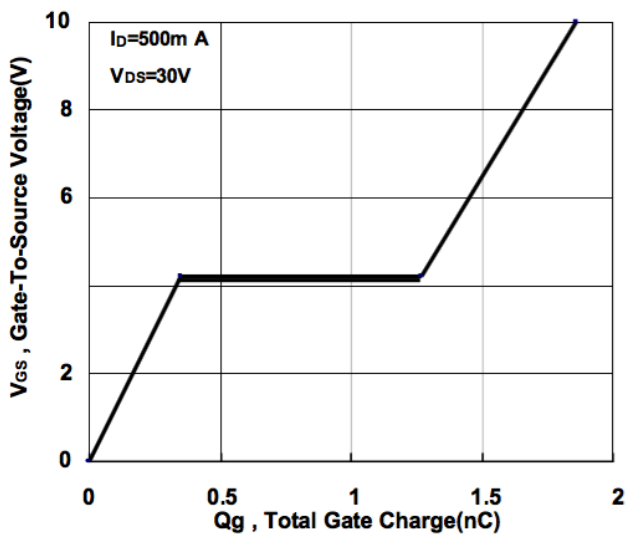
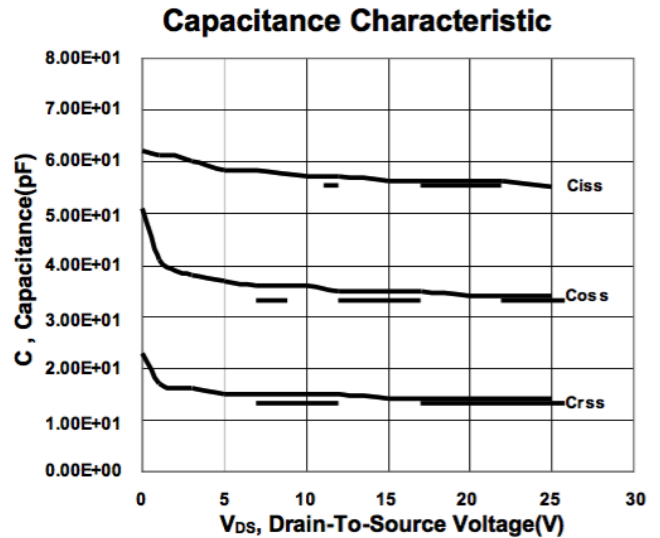
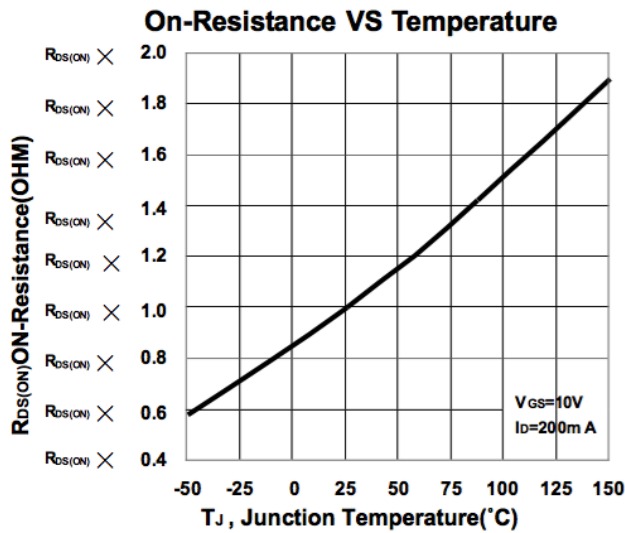
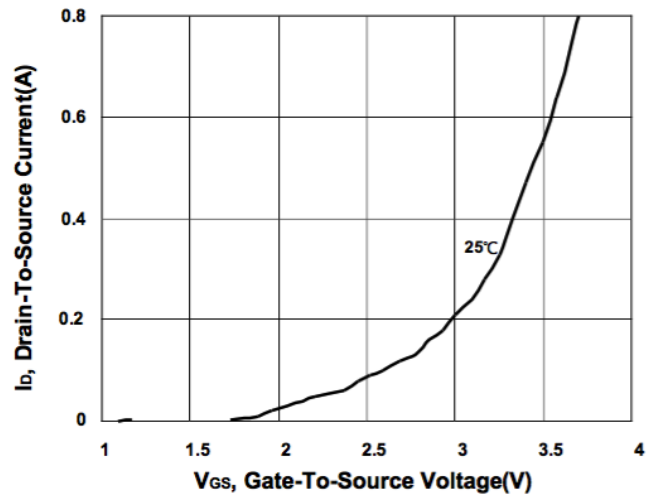
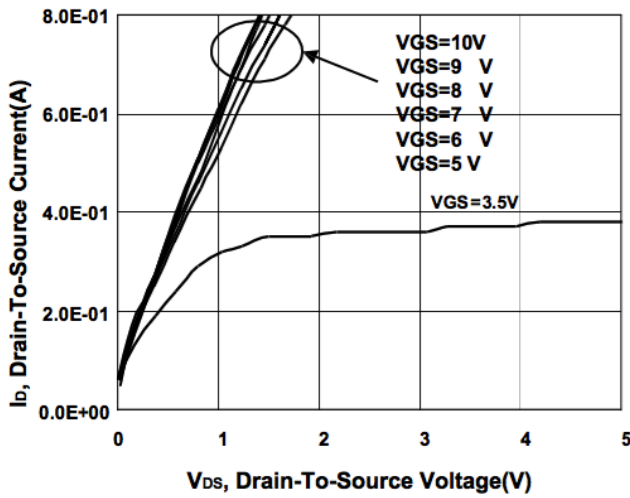
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	-0.3	A
I_{SM}	Pulsed Source Current ^{2,4}		---	---	-1	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ\text{C}$	---	---	-1.2	V

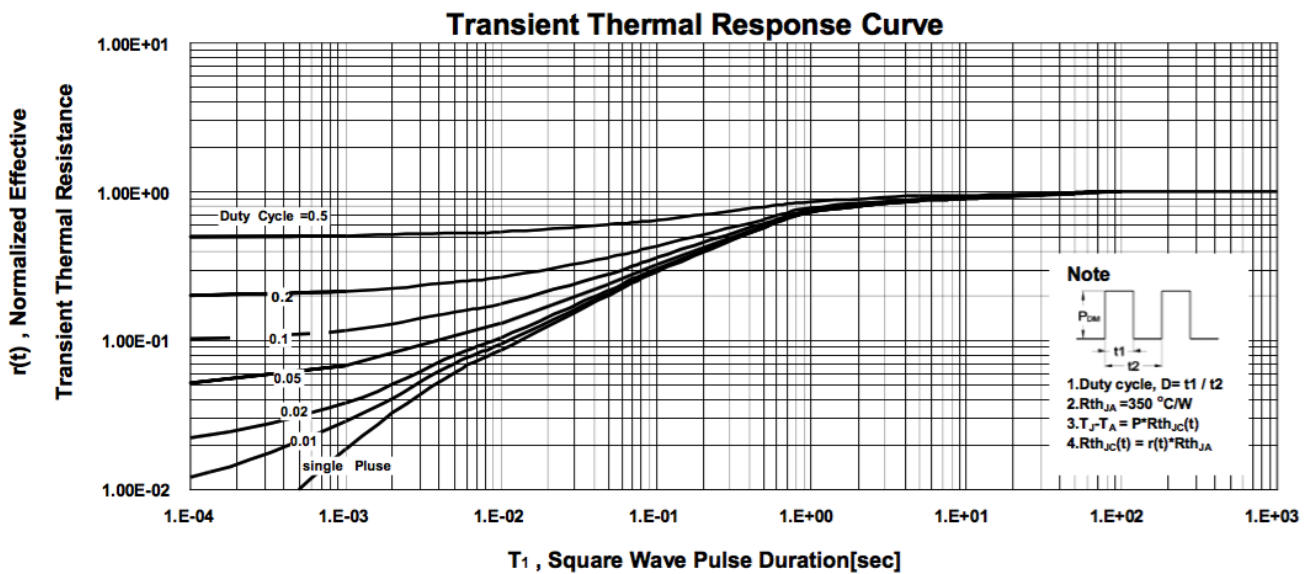
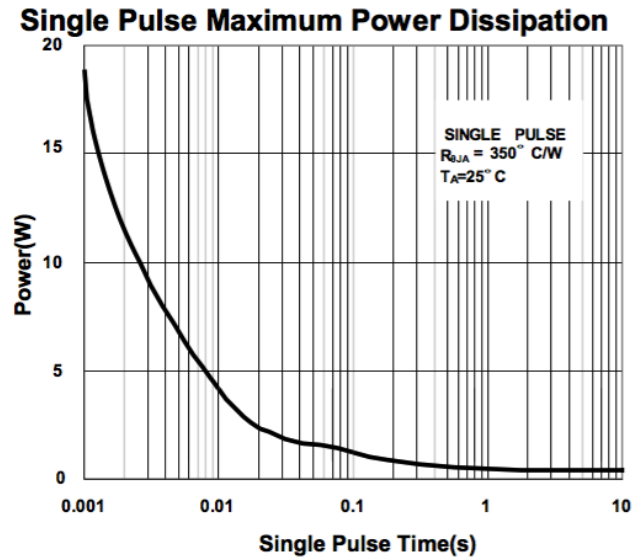
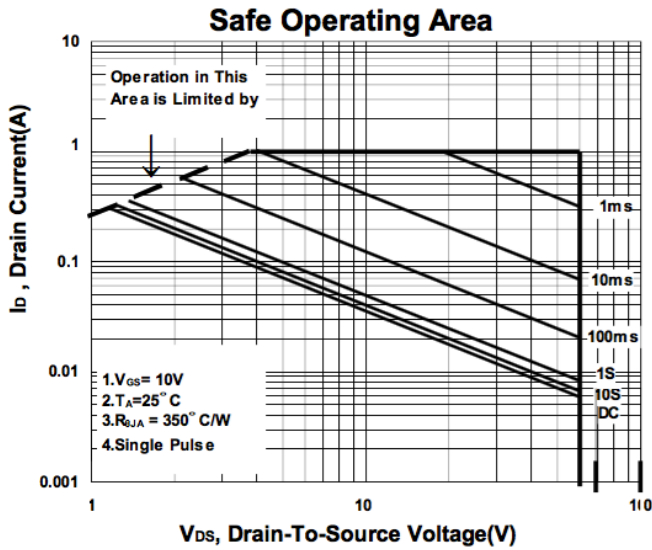
Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



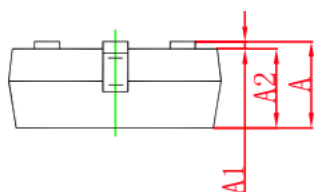
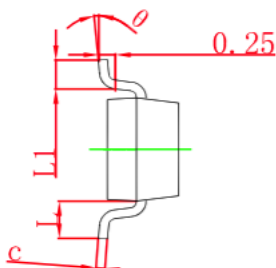
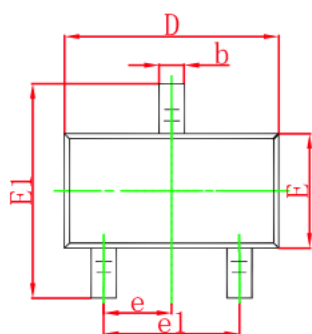
Typical Characteristics





Ordering Information

Part Number	Package code	Packaging
BSS84	SOT-23	3000/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°